N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

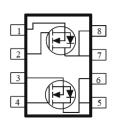
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
30	$13.5 @ V_{GS} = 4.5V$	10		
	$20 @ V_{GS} = 2.5V$	8		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Symbol	Limit	Units	
Drain-Source Voltage			V_{DS}	30	V	
Gate-Source Voltage			V_{GS}	±8	V	
Continuos Durin Commenta		T _A =25°C	1	10		
Continuous Drain Current ^a		T _A =70°C	I _D	8.1	Α	
Pulsed Drain Current ^b				40		
Continuous Source Current (Diode Conduction) a				3.3	Α	
Power Dissipation ^a		T _A =25°C	P _D	2.1	W	
Power dissipation		T _A =70°C	' D	1.3	VV	
Operating Junction and Storage Temperature Range			T_J,T_sta	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Ambient	Steady State	IXOJA	110			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

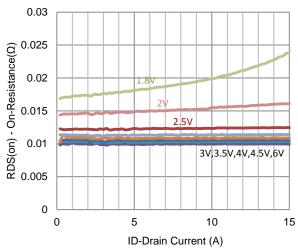
Parameter	Symbol	ool Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	— uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5.1			Α	
Drain-Source On-Resistance	r	$V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$			13.5	mΩ	
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 6.8 \text{ A}$			20	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 8 \text{ A}$		8		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 1.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.68		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		24		nC	
Gate-Source Charge	Q_{gs}	$I_{D} = 8 \text{ A}$		5.0			
Gate-Drain Charge	Q_gd	1D = 0 A		6.8			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_1 = 1.9 \Omega,$		19			
Rise Time	t _r	$V_{DS} = 13 \text{ V}, K_L - 1.9 \Omega,$ $I_D = 8 \text{ A},$		25		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		105		ns	
Fall Time	t _f	V GEN - 4.5 V, T GEN - 0 12		33			
Input Capacitance	C _{iss}			2141			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		229		pF	
Reverse Transfer Capacitance	C_{rss}]		205			

Notes

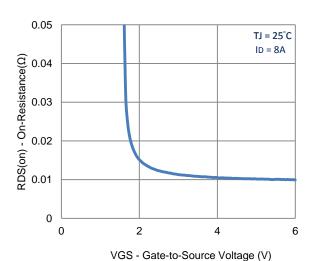
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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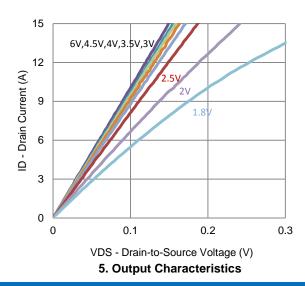
Typical Electrical Characteristics

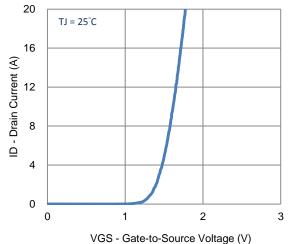


1. On-Resistance vs. Drain Current

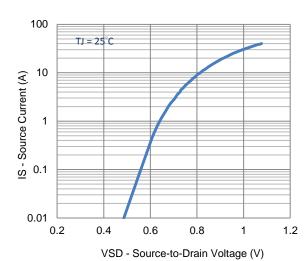


3. On-Resistance vs. Gate-to-Source Voltage

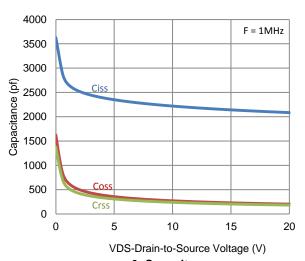




2. Transfer Characteristics

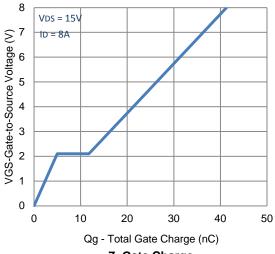


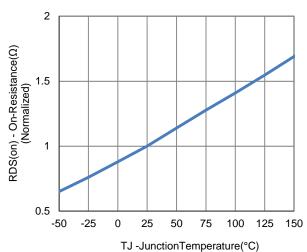
4. Drain-to-Source Forward Voltage



6. Capacitance

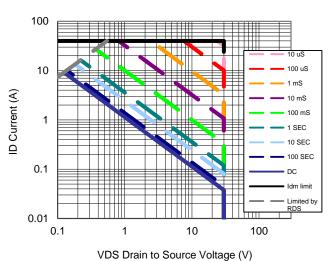
Typical Electrical Characteristics

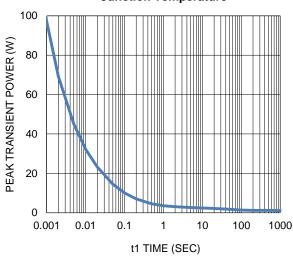




7. Gate Charge

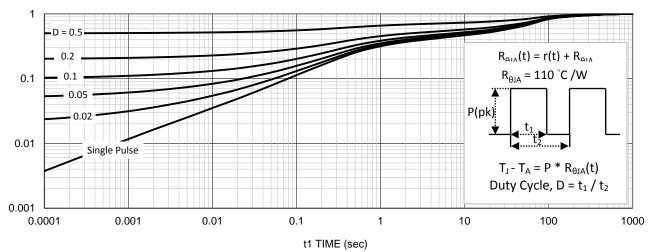






9. Safe Operating Area

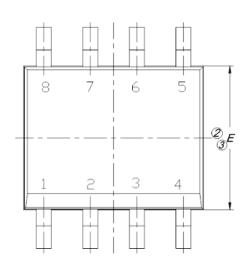
10. Single Pulse Maximum Power Dissipation

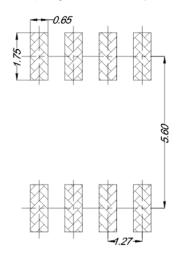


11. Normalized Thermal Transient Junction to Ambient

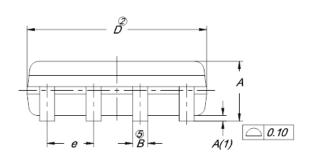
Package Information

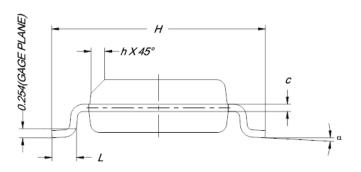
Land Pattern (Only for Reference)





DIM.	MILLIMETERS					
	MIN.	NOM.	MAX.			
Α	1.35	1.55	1.75			
A(1)	0.10	0.18	0.25			
В	0.38	0.45	0.51			
С	0.19	0.22	0.25			
D	4.80	4.90	5.00			
E	3.80	3.90	4.00			
е	1.27 BSC					
Н	5.80	6.00	6.20			
L	0.50	0.72	0.93			
α	0°	4°	8°			
h	0.25	0.38	0.50			





Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.